



SHENZHEN HAOLIN ELECTRONICS TECHNOLOGY CO., LTD

TO-92 Plastic-Encapsulate Transistors

2N5551 TRANSISTOR (NPN)

FEATURES

Power dissipation

$$P_{CM} : 0.625 \text{ W (} T_{amb}=25 \text{)}$$

Collector current

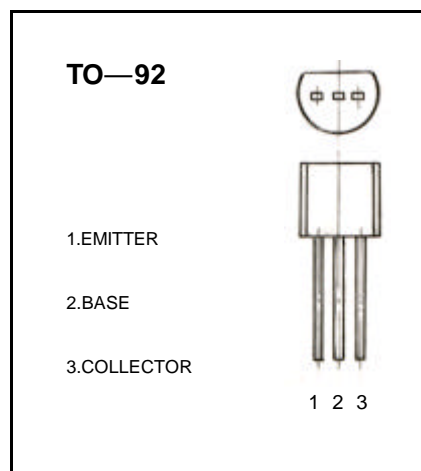
$$I_{CM} : 0.6 \text{ A}$$

Collector-base voltage

$$V_{(BR)CBO} : 180 \text{ V}$$

Operating and storage junction temperature range

$$T_J, T_{stg} : -55 \text{ to } +150$$



ELECTRICAL CHARACTERISTICS ($T_{amb}=25$ unless otherwise specified)

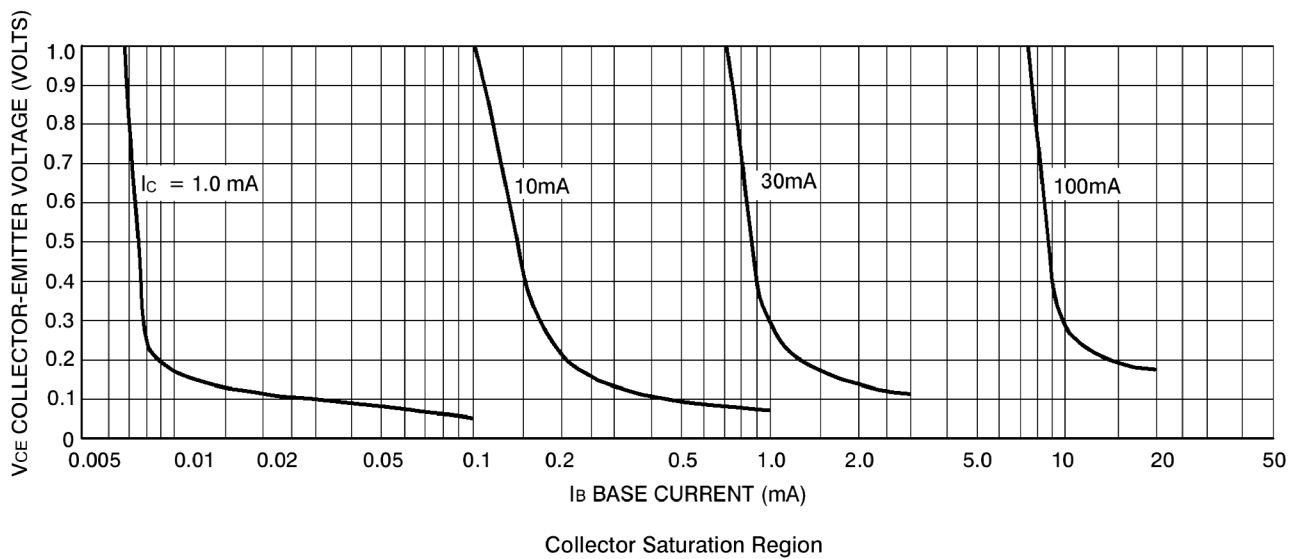
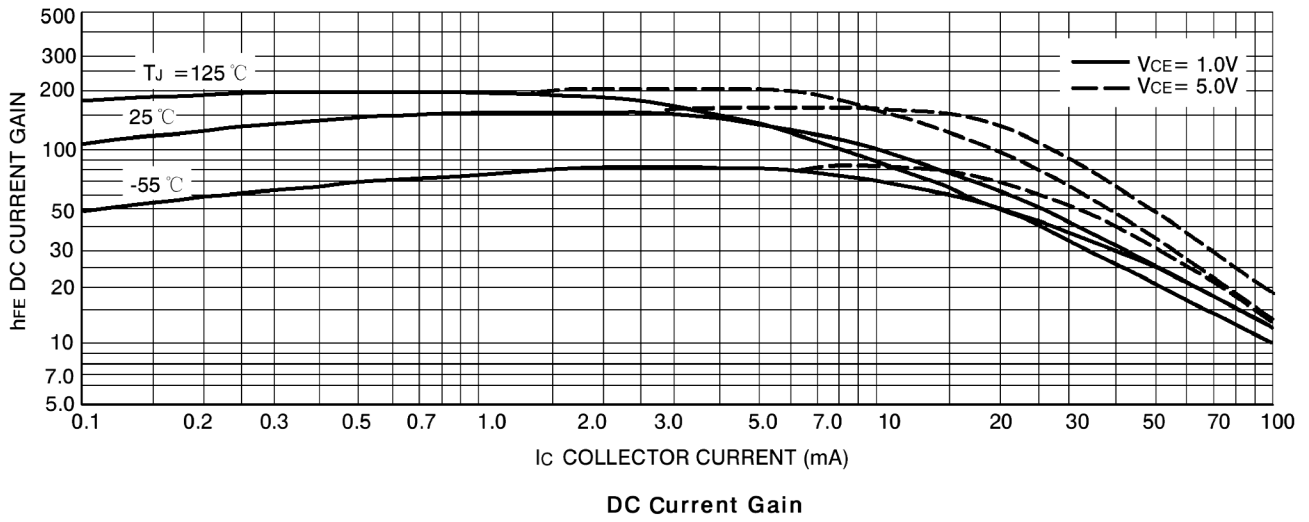
Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = 100 \mu A, I_E = 0$	180			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 100 \mu A, I_B = 0$	160			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 100 \mu A, I_C = 0$	6			V
Collector cut-off current	I_{CBO}	$V_{CB} = 180V, I_E = 0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 4 \text{ V}, I_C = 0$			0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = 5 \text{ V}, I_C = 1 \text{ mA}$	80			
	$h_{FE(2)}$	$V_{CE} = 5 \text{ V}, I_C = 10 \text{ mA}$	80		250	
	$h_{FE(3)}$	$V_{CE} = 5 \text{ V}, I_C = 50 \text{ mA}$	50			
Collector-emitter saturation voltage	V_{CEsat}	$I_C = 50 \text{ mA}, I_B = 5 \text{ mA}$			0.5	V
Base-emitter saturation voltage	V_{BEsat}	$I_C = 50 \text{ mA}, I_B = 5 \text{ mA}$			1	V
Transition frequency	f_T	$V_{CE} = 5 \text{ V}, I_C = 10 \text{ mA}, f = 30 \text{ MHz}$	80			MHz

CLASSIFICATION OF $h_{FE(2)}$

Rank	A	B	C
Range	80-160	120-180	150-250

Typical Characteristics

2N5551



TO-92 PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	3.300	3.700	0.130	0.146
A1	1.100	1.400	0.043	0.055
b	0.380	0.550	0.015	0.022
c	0.360	0.510	0.014	0.020
D	4.400	4.700	0.173	0.185
D1	3.430		0.135	
E	4.300	4.700	0.169	0.185
e	1.270TYP		0.050TYP	
e1	2.440	2.640	0.096	0.104
L	14.100	14.500	0.555	0.571
Ö		1.600		0.063
↓	0.000	0.380	0.000	0.015